

Silicon NPN Power Transistors

2SC2168

DESCRIPTION

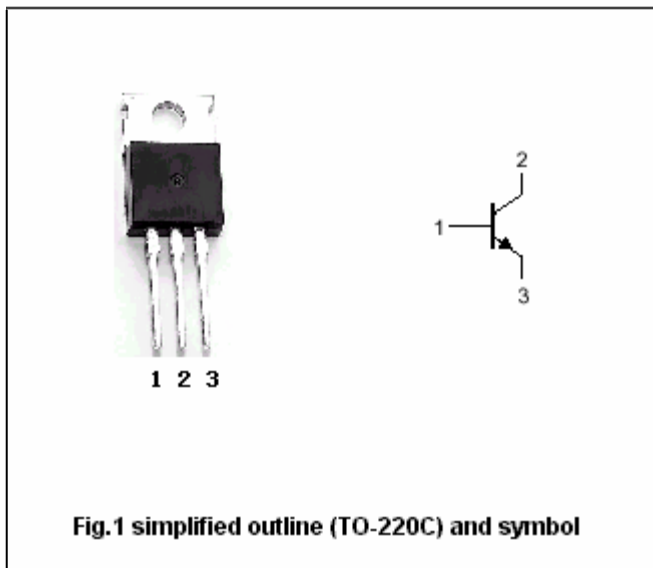
- With TO-220 package
- High collector-emitter breakdown voltage  
:  $V_{CEO}=200V(\text{min})$

APPLICATIONS

- Power amplifier applications
- TV vertical deflection applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	200	V
$V_{CEO}$	Collector-emitter voltage	Open base	200	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		2	A
$I_{CM}$	Collector current-peak		3	A
$P_C$	Collector power dissipation	$T_C=25$	30	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =25mA ; I <sub>B</sub> =0	200			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =0.5mA ; I <sub>E</sub> =0	200			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =0.5mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A ; I <sub>B</sub> =50m A			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	50			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		20		MHz

固电半导体

INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE

